BC856BDW1T1G, SBC856BDW1T1G Series, BC857BDW1T1G, SBC857BDW1T1G Series, BC858CDW1T1G Series

Dual General Purpose Transistors

PNP Duals

These transistors are designed for general purpose amplifier applications. They are housed in the SOT−363/SC−88 which is designed for low power surface mount applications.

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector−Emitter Voltage BC856, SBC856 BC857, SBC857 BC858	V_{CEO}	 −65 −45 −30	V
Collector−Base Voltage BC856, SBC856 BC857, SBC857 BC858	V_{CBO}	 −80 −50 −30	V
Emitter−Base Voltage	V_{EBO}	−5.0	V
Collector Current −Continuous	I_C	−100	mAdc
Collector Current − Peak	I_C	−200	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation Per Device FR−5 Board (Note 1) T_A = 25°C Derate Above 25°C	P_D	380 250 3.0	mW mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	 328	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

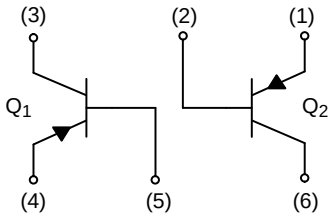
1. FR−5 = 1.0 x 0.75 x 0.062 in

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

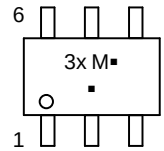
ON Semiconductor®

www.onsemi.com

SOT−363/SC−88
CASE 419B
STYLE 1



MARKING DIAGRAM



3x = Specific Device Code
x = B, F, G, or L
(See Ordering Information)
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector−Emitter Breakdown Voltage (I_C = −10 mA)	$V_{(BR)CEO}$				V
BC856, SBC856 Series		−65	−	−	
BC857, SBC857 Series		−45	−	−	
BC858 Series		−30	−	−	
Collector−Emitter Breakdown Voltage (I_C = −10 μA, V_{EB} = 0)	$V_{(BR)CES}$				V
BC856, SBC856 Series		−80	−	−	
BC857B, SBC857B Only		−50	−	−	
BC858 Series		−30	−	−	
Collector−Base Breakdown Voltage (I_C = −10 μA)	$V_{(BR)CBO}$				V
BC856, SBC856 Series		−80	−	−	
BC857, SBC857 Series		−50	−	−	
BC858 Series		−30	−	−	
Emitter−Base Breakdown Voltage (I_E = −1.0 μA)	$V_{(BR)EBO}$				V
BC856, SBC856 Series		−5.0	−	−	
BC857, SBC857 Series		−5.0	−	−	
BC858 Series		−5.0	−	−	
Collector Cutoff Current	I_{CBO}				
(V_{CB} = −30 V)		−	−	−15	nA
(V_{CB} = −30 V, T_A = 150°C)		−	−	−4.0	μA
ON CHARACTERISTICS					
DC Current Gain	h_{FE}				−
(I_C = −10 μA, V_{CE} = −5.0 V)					
BC856B, SBC856B, BC857B, SBC857B		−	150	−	
BC857C, SBC857C, BC858C		−	270	−	
(I_C = −2.0 mA, V_{CE} = −5.0 V)					
BC856B, SBC856B, BC857B, SBC857B		220	290	475	
BC857C, SBC857C, BC858C		420	520	800	
Collector−Emitter Saturation Voltage	$V_{CE(sat)}$				V
(I_C = −10 mA, I_B = −0.5 mA)		−	−	−0.3	
(I_C = −100 mA, I_B = −5.0 mA)		−	−	−0.65	
Base−Emitter Saturation Voltage	$V_{BE(sat)}$				V
(I_C = −10 mA, I_B = −0.5 mA)		−	−0.7	−	
(I_C = −100 mA, I_B = −5.0 mA)		−	−0.9	−	
Base−Emitter On Voltage	$V_{BE(on)}$				V
(I_C = −2.0 mA, V_{CE} = −5.0 V)		−0.6	−	−0.75	
(I_C = −10 mA, V_{CE} = −5.0 V)		−	−	−0.82	
SMALL−SIGNAL CHARACTERISTICS					
Current−Gain − Bandwidth Product (I_C = −10 mA, V_{CE} = −5.0 Vdc, f = 100 MHz)	f_T	100	−	−	MHz
Output Capacitance (V_{CB} = −10 V, f = 1.0 MHz)	C_{ob}	−	−	4.5	pF
Noise Figure (I_C = −0.2 mA, V_{CE} = −5.0 Vdc, R_S = 2.0 kΩ, f = 1.0 kHz, BW = 200 Hz)	NF	−	−	10	dB

TYPICAL CHARACTERISTICS − BC856/SBC856

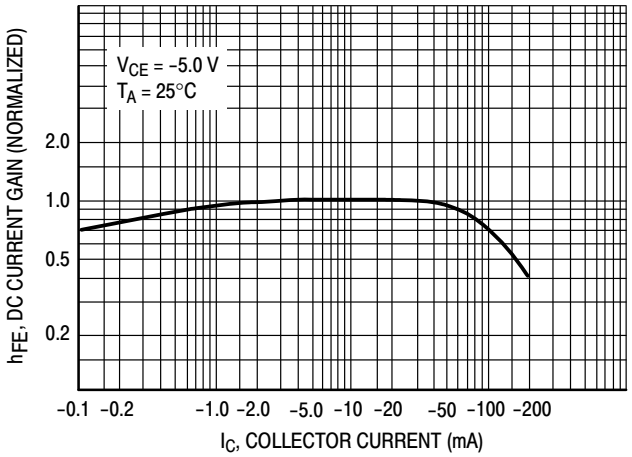


Figure 1. DC Current Gain

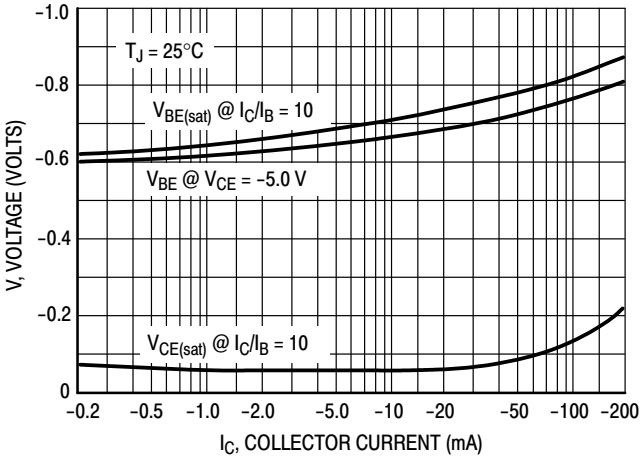


Figure 2. “On” Voltage

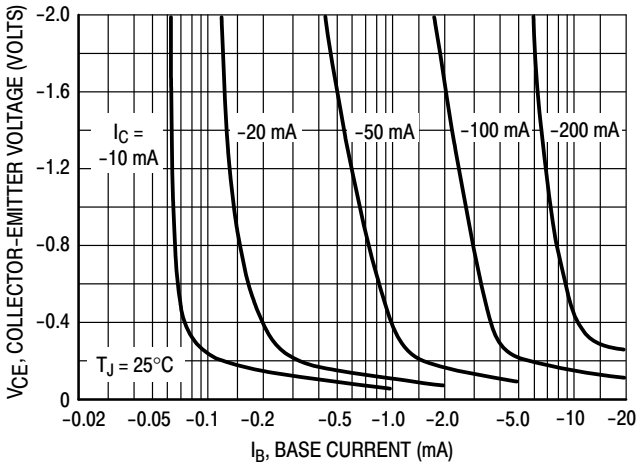


Figure 3. Collector Saturation Region

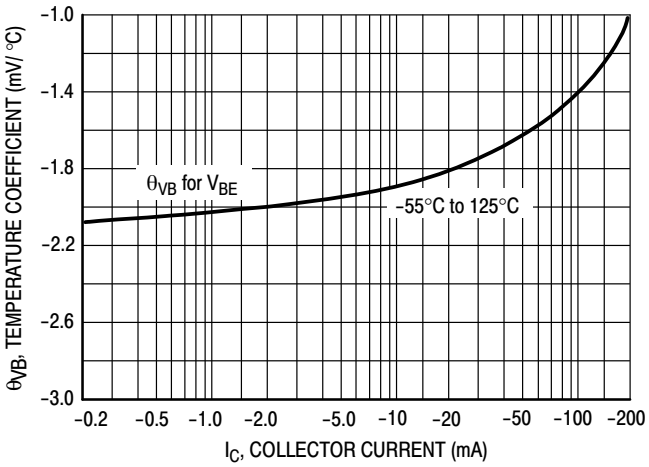


Figure 4. Base−Emitter Temperature Coefficient

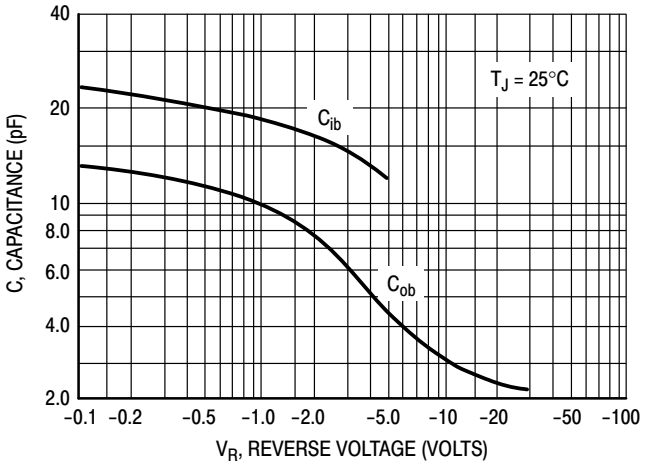


Figure 5. Capacitance

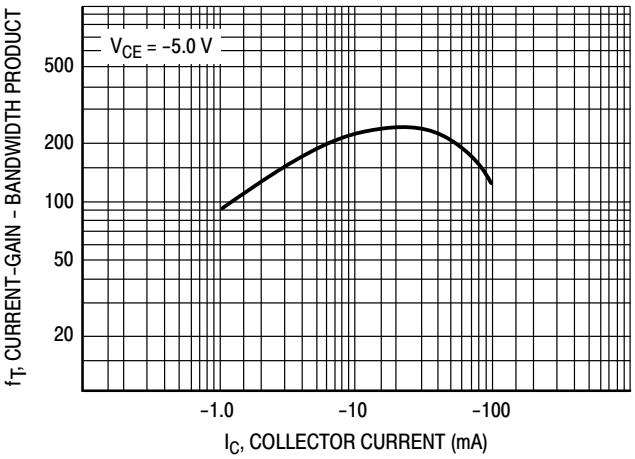


Figure 6. Current−Gain − Bandwidth Product

TYPICAL CHARACTERISTICS − BC857/SBC857/BC858

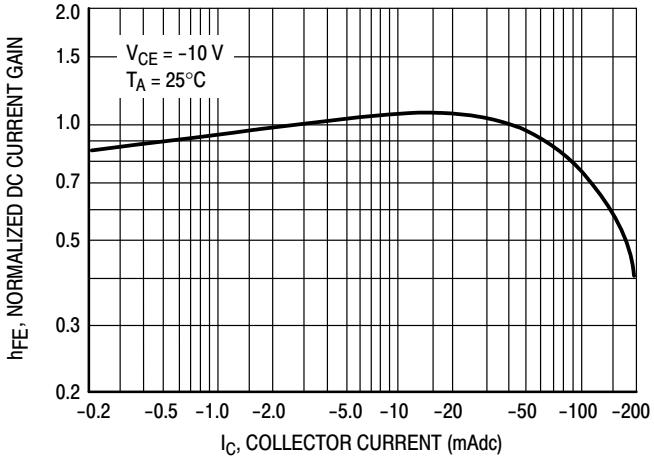


Figure 7. Normalized DC Current Gain

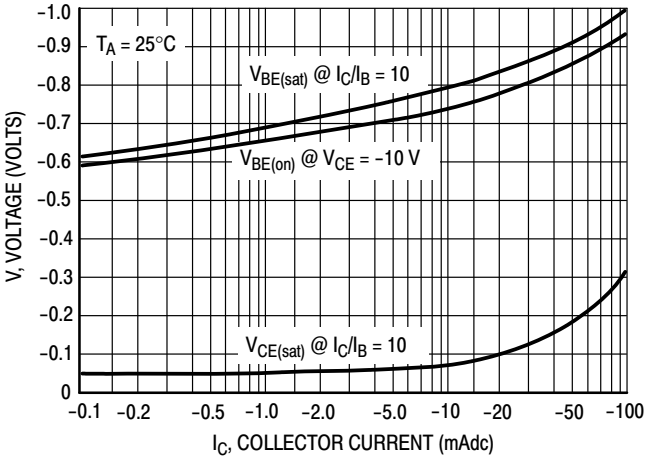


Figure 8. "Saturation" and "On" Voltages

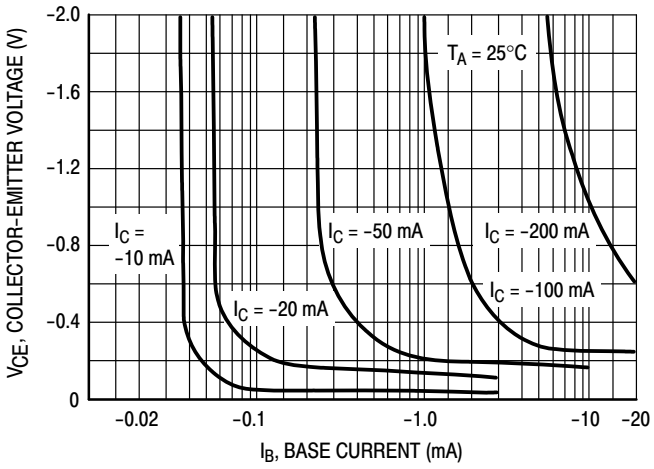


Figure 9. Collector Saturation Region

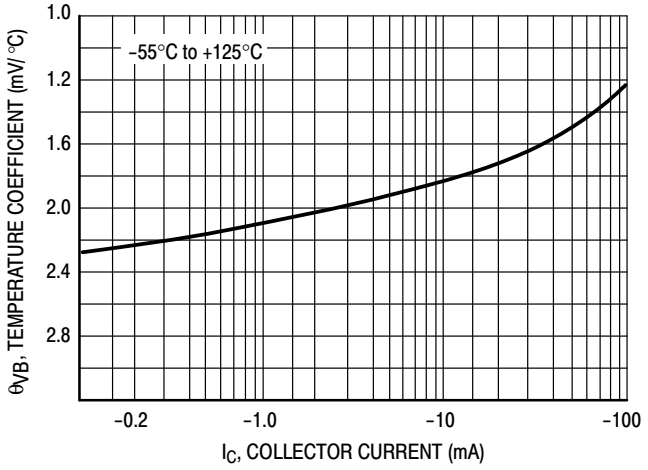


Figure 10. Base−Emitter Temperature Coefficient

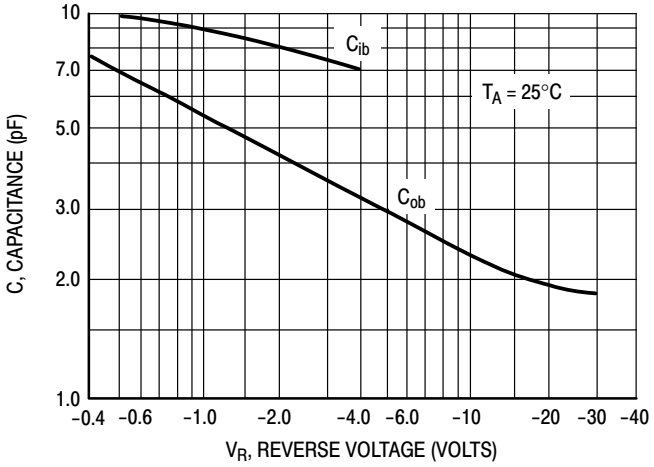


Figure 11. Capacitances

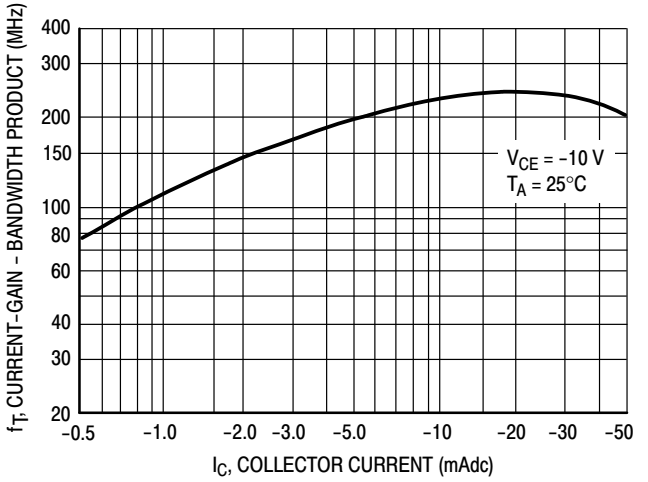


Figure 12. Current−Gain − Bandwidth Product

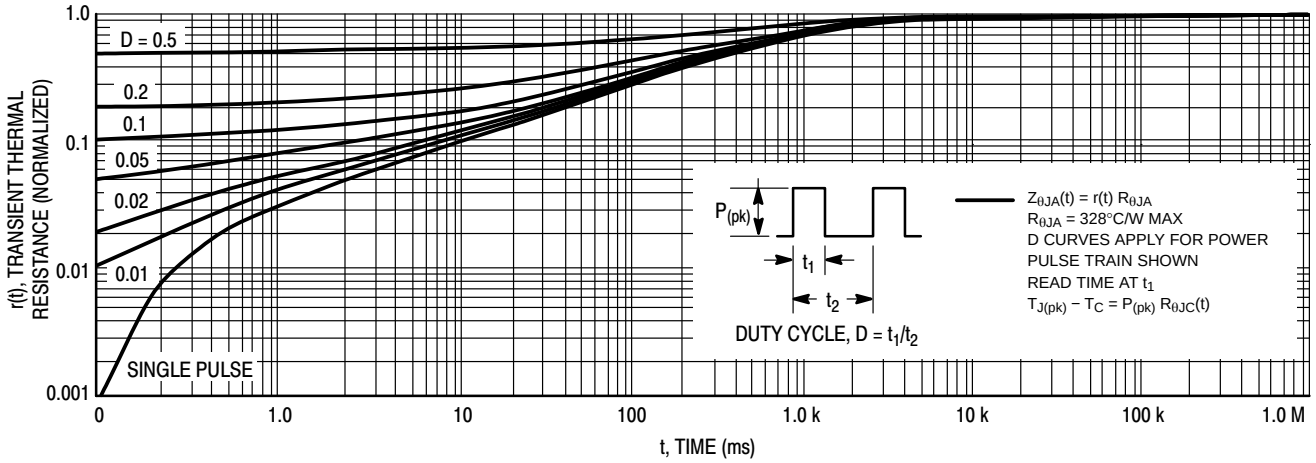


Figure 13. Thermal Response

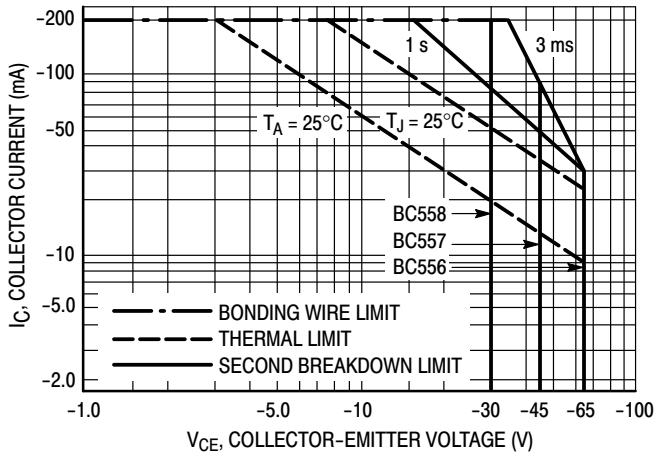


Figure 14. Active Region Safe Operating Area

The safe operating area curves indicate I_C−V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 14 is based upon $T_{J(pk)}$ = 150°C; T_C or T_A is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150°C$. $T_{J(pk)}$ may be calculated from the data in Figure 13. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by the secondary breakdown.

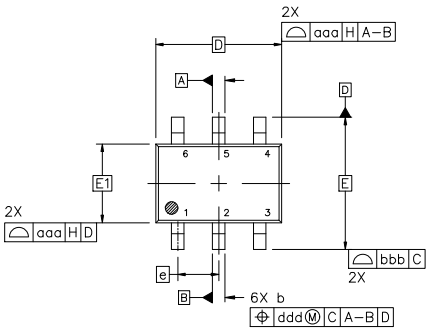
ORDERING INFORMATION

Device	Device Marking	Package	Shipping†
BC856BDW1T1G	3B	SOT−363 (Pb−Free)	3,000 / Tape & Reel
SBC856BDW1T1G	3B	SOT−363 (Pb−Free)	3,000 / Tape & Reel
BC856BDW1T3G	3B	SOT−363 (Pb−Free)	10,000 / Tape & Reel
SBC856BDW1T3G	3B	SOT−363 (Pb−Free)	10,000 / Tape & Reel
BC857BDW1T1G	3F	SOT−363 (Pb−Free)	3,000 / Tape & Reel
SBC857BDW1T1G	3F	SOT−363 (Pb−Free)	3,000 / Tape & Reel
BC857CDW1T1G	3G	SOT−363 (Pb−Free)	3,000 / Tape & Reel
SBC857CDW1T1G	3G	SOT−363 (Pb−Free)	3,000 / Tape & Reel
BC858CDW1T1G	3L	SOT−363 (Pb−Free)	3,000 / Tape & Reel

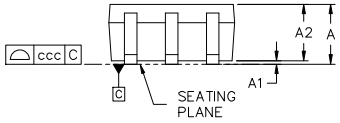
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

SC−88 2.00x1.25x0.90, 0.65P
CASE 419B−02
ISSUE Z

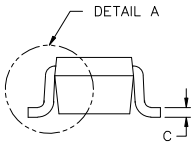
DATE 18 APR 2024



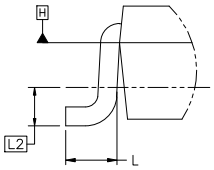
TOP VIEW



SIDE VIEW



END VIEW

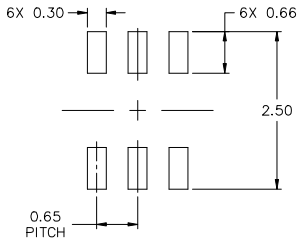


DETAIL A
SCALE 2:1

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5−2018.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

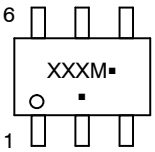
	MILLIMETERS		
DIM	MIN.	NOM.	MAX.
A	−−−	−−−	1.10
A1	0.00	−−−	0.10
A2	0.70	0.90	1.00
b	0.15	0.20	0.25
c	0.08	0.15	0.22
D	2.00 BSC		
E	2.10 BSC		
E1	1.25 BSC		
e	0.65 BSC		
L	0.26	0.36	0.46
L2	0.15 BSC		
aaa	0.15		
bbb	0.30		
ccc	0.10		
ddd	0.10		



RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb−FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

DOCUMENT NUMBER:	**98ASB42985B**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.	
DESCRIPTION:	**SC−88 2.00x1.25x0.90, 0.65P**		**PAGE 1 OF 2**

SC−88 2.00x1.25x0.90, 0.65P
CASE 419B−02
ISSUE Z

DATE 18 APR 2024

STYLE 1:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

STYLE 2:
CANCELLED

STYLE 3:
CANCELLED

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. COLLECTOR
4. EMITTER
5. BASE
6. ANODE

STYLE 5:
PIN 1. ANODE
2. ANODE
3. COLLECTOR
4. EMITTER
5. BASE
6. CATHODE

STYLE 6:
PIN 1. ANODE 2
2. N/C
3. CATHODE 1
4. ANODE 1
5. N/C
6. CATHODE 2

STYLE 7:
PIN 1. SOURCE 2
2. DRAIN 2
3. GATE 1
4. SOURCE 1
5. DRAIN 1
6. GATE 2

STYLE 8:
CANCELLED

STYLE 9:
PIN 1. EMITTER 2
2. EMITTER 1
3. COLLECTOR 1
4. BASE 1
5. BASE 2
6. COLLECTOR 2

STYLE 10:
PIN 1. SOURCE 2
2. SOURCE 1
3. GATE 1
4. DRAIN 1
5. DRAIN 2
6. GATE 2

STYLE 11:
PIN 1. CATHODE 2
2. CATHODE 2
3. ANODE 1
4. CATHODE 1
5. CATHODE 1
6. ANODE 2

STYLE 12:
PIN 1. ANODE 2
2. ANODE 2
3. CATHODE 1
4. ANODE 1
5. ANODE 1
6. CATHODE 2

STYLE 13:
PIN 1. ANODE
2. N/C
3. COLLECTOR
4. EMITTER
5. BASE
6. CATHODE

STYLE 14:
PIN 1. VREF
2. GND
3. GND
4. IOUT
5. VEN
6. VCC

STYLE 15:
PIN 1. ANODE 1
2. ANODE 2
3. ANODE 3
4. CATHODE 3
5. CATHODE 2
6. CATHODE 1

STYLE 16:
PIN 1. BASE 1
2. EMITTER 2
3. COLLECTOR 2
4. BASE 2
5. EMITTER 1
6. COLLECTOR 1

STYLE 17:
PIN 1. BASE 1
2. EMITTER 1
3. COLLECTOR 2
4. BASE 2
5. EMITTER 2
6. COLLECTOR 1

STYLE 18:
PIN 1. VIN1
2. VCC
3. VOUT2
4. VIN2
5. GND
6. VOUT1

STYLE 19:
PIN 1. I OUT
2. GND
3. GND
4. V CC
5. V EN
6. V REF

STYLE 20:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR

STYLE 21:
PIN 1. ANODE 1
2. N/C
3. ANODE 2
4. CATHODE 2
5. N/C
6. CATHODE 1

STYLE 22:
PIN 1. D1 (i)
2. GND
3. D2 (i)
4. D2 (c)
5. VBUS
6. D1 (c)

STYLE 23:
PIN 1. Vn
2. CH1
3. Vp
4. N/C
5. CH2
6. N/C

STYLE 24:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE

STYLE 25:
PIN 1. BASE 1
2. CATHODE
3. COLLECTOR 2
4. BASE 2
5. EMITTER
6. COLLECTOR 1

STYLE 26:
PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

STYLE 27:
PIN 1. BASE 2
2. BASE 1
3. COLLECTOR 1
4. EMITTER 1
5. EMITTER 2
6. COLLECTOR 2

STYLE 28:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

STYLE 29:
PIN 1. ANODE
2. ANODE
3. COLLECTOR
4. EMITTER
5. BASE/ANODE
6. CATHODE

STYLE 30:
PIN 1. SOURCE 1
2. DRAIN 2
3. DRAIN 2
4. SOURCE 2
5. GATE 1
6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

DOCUMENT NUMBER:	**98ASB42985B**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	**SC−88 2.00x1.25x0.90, 0.65P**		**PAGE 2 OF 2**

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales